

$\frac{d}{dt} \left(\frac{\partial L}{\partial \dot{x}} \right) = \frac{\partial L}{\partial x}$

5 portion has at least one step for controlling a density of the plasma formed by the electrode. The electrode can be used as the grounded upper electrode in a parallel plate plasma processing apparatus such as a plasma etching apparatus. The geometric features of the step and of a corresponding edge ring on the lower electrode can be varied to achieve the desired etch rate profile across a wafer

0 surface.